



P-Channel 2.5-V (G-S) MOSFET

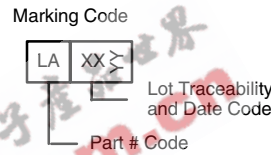
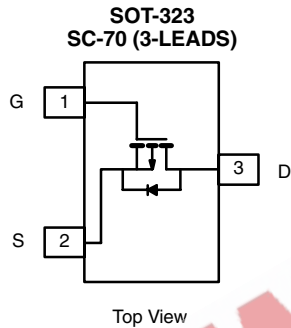
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 20	0.430 at $V_{GS} = - 4.5$ V	- 0.72
	0.480 at $V_{GS} = - 3.6$ V	- 0.68
	0.700 at $V_{GS} = - 2.5$ V	- 0.56

FEATURES

- TrenchFET[®] Power MOSFETs
- 2.5 V Rated



Available
RoHS*
COMPLIANT



Ordering Information: Si1303DL-T1
Si1303DL-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted					
Parameter	Symbol	5 sec	Steady State	Unit	
Drain-Source Voltage	V_{DS}	- 20		V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	- 0.72	- 0.67	A
	$T_A = 70^\circ\text{C}$		- 0.58	- 0.54	
Pulsed Drain Current		I_{DM}	- 2.5		
Continuous Diode Current (Diode Conduction) ^a		I_S	- 0.28	- 0.24	W
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	0.34	0.29	
	$T_A = 70^\circ\text{C}$		0.22	0.19	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 5$ sec	315	375	$^\circ\text{C/W}$
		Steady State	360	430	
Maximum Junction-to-Foot (Drain)	R_{thJF}	285	340		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

Si1303DL

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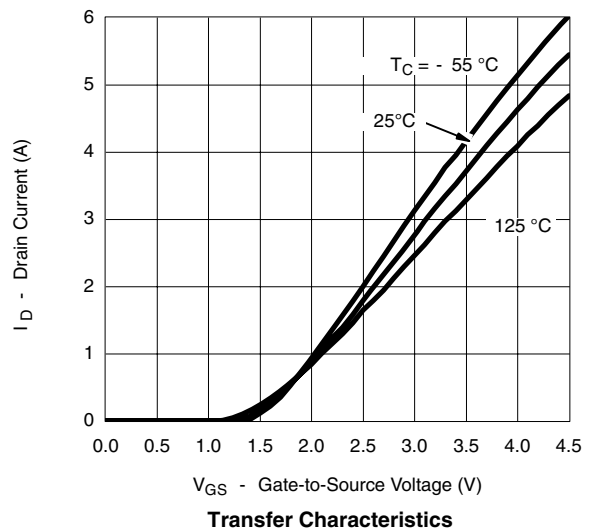
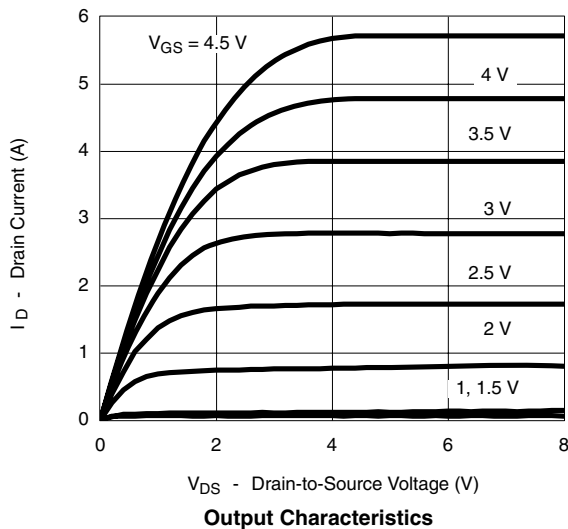
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.6		- 1.4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			- 5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 2.5			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		0.360	0.430	Ω
		$V_{GS} = -3.6\text{ V}, I_D = -0.7\text{ A}$		0.400	0.480	
		$V_{GS} = -2.5\text{ V}, I_D = -0.3\text{ A}$		0.560	0.700	
Forward Transconductance ^a	g_{fs}	$V_{GS} = -10\text{ V}, I_D = -1\text{ A}$		1.7		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.3\text{ A}, V_{GS} = 0\text{ V}$			- 1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1\text{ A}$		1.7	2.2	nC
Gate-Source Charge	Q_{gs}		0.38			
Gate-Drain Charge	Q_{gd}		0.63			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		9	15	ns
Rise Time	t_r			31	45	
Turn-Off Delay Time	$t_{d(off)}$			12.5	20	
Fall Time	t_f			14	20	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = -1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		35	

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

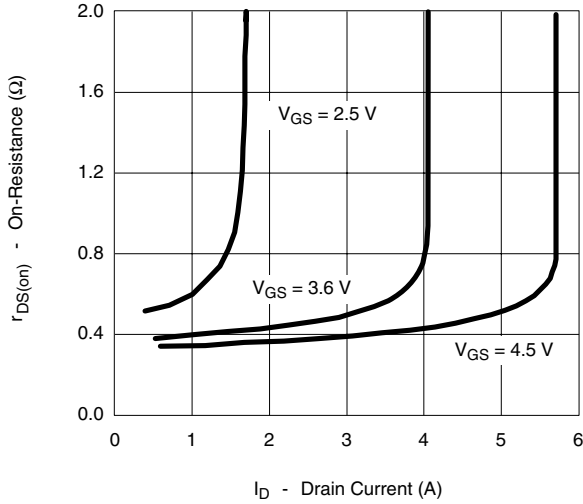
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless noted

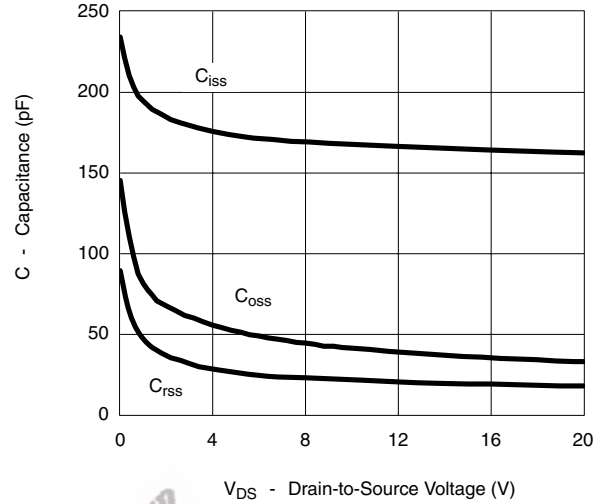




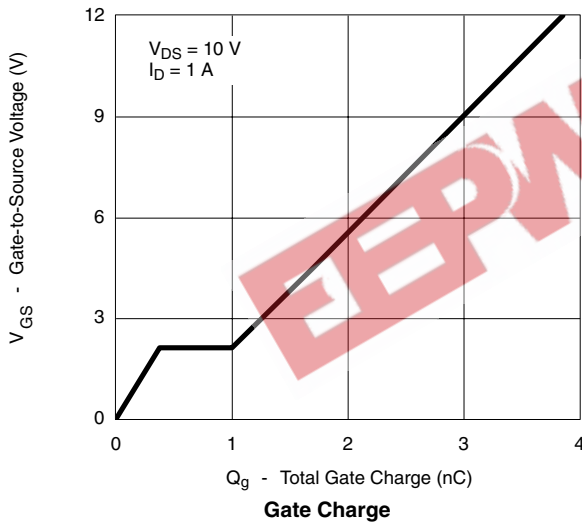
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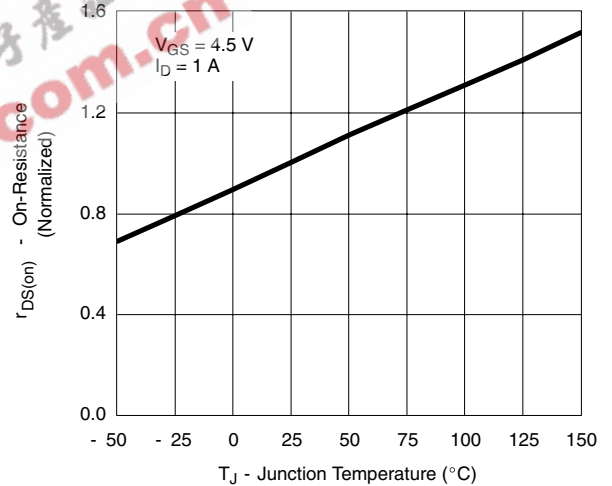
On-Resistance vs. Drain Current



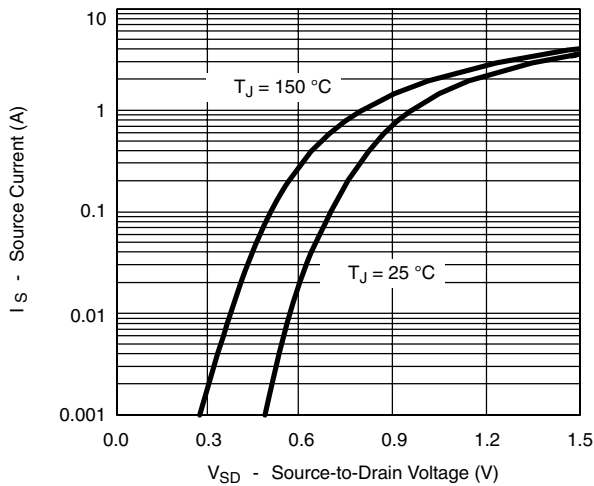
Capacitance



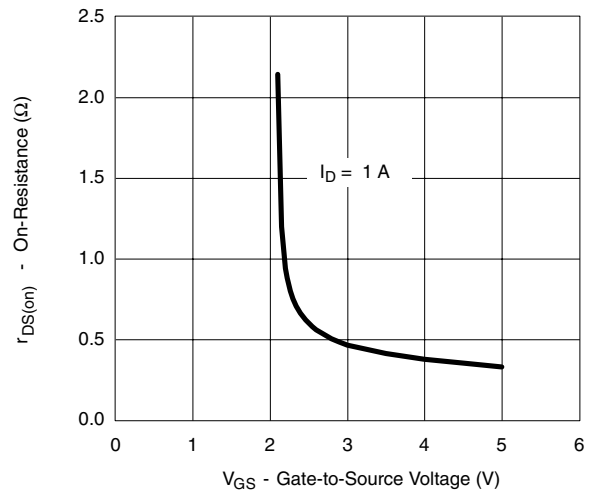
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



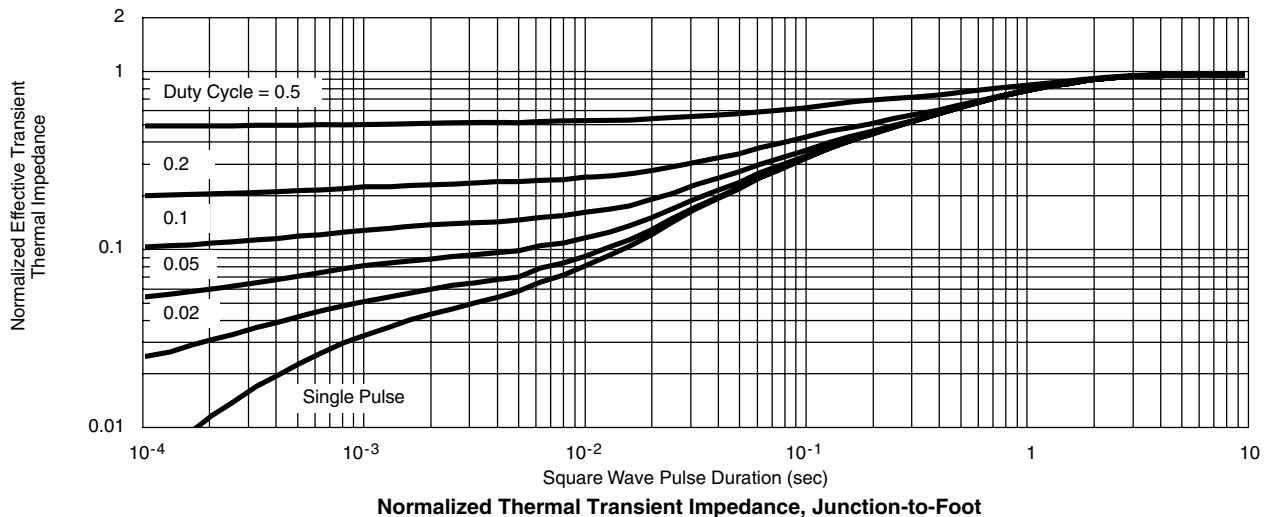
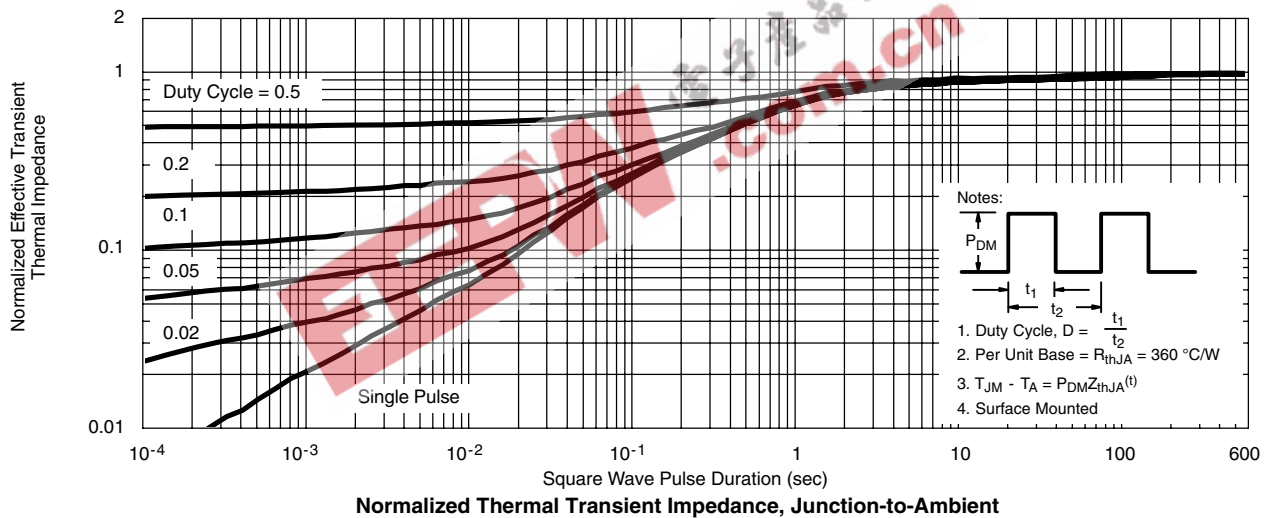
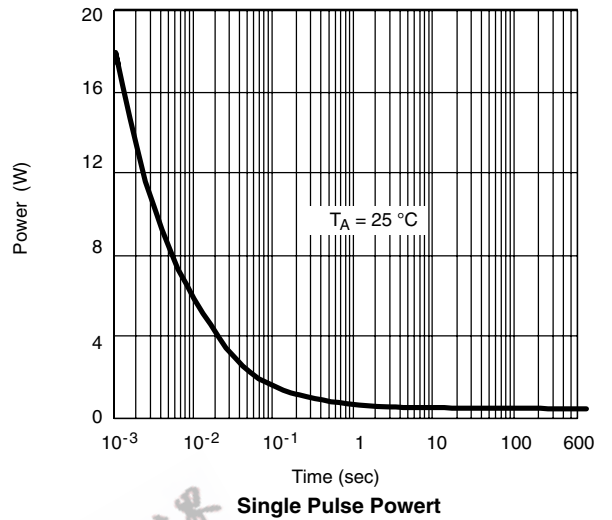
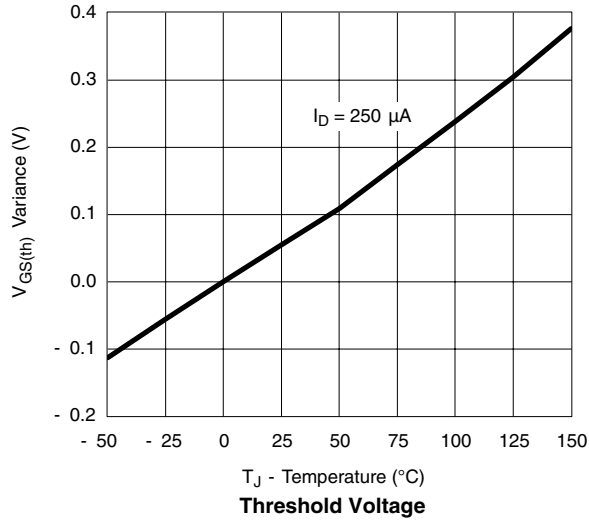
On-Resistance vs. Gate-to-Source Voltage

Si1303DL

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TYPICAL CHARACTERISTICS 25 °C, unless noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?71075>.



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